# DMG26412

## Silicon NPN epitaxial planar type (Tr1) Silicon PNP epitaxial planar type (Tr2)

For digital circuits

#### Features

- $\bullet$  Low collector-emitter saturation voltage  $V_{\mbox{CE(sat)}}$
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

Marking Symbol: S9

#### Basic Part Number

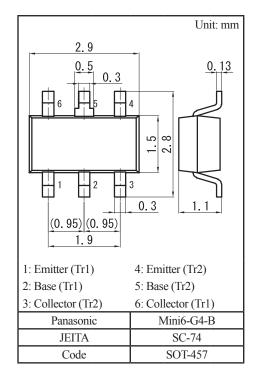
DRC2543E + DRA2543E (Individual)

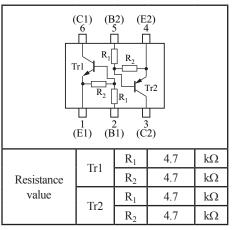
#### Packaging

DMG264120R Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

#### Absolute Maximum Ratings $T_a = 25^{\circ}C$

	Parameter		Rating	Unit	
Tr1	Collector-base voltage (Emitter open)	V <sub>CBO</sub>	50	V	
	Collector-emitter voltage (Base open)	V <sub>CEO</sub>	50	V	
	Collector current	I <sub>C</sub>	500	mA	
Tr2	Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-50	V	
	Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-50	V	
	Collector current	I <sub>C</sub>	-500	mA	
Overall	Total power dissipation	P <sub>T</sub>	300	mW	
	Junction temperature	Tj	150	°C	
	Operating ambient temperature	T <sub>opr</sub>	-40 to +85	°C	
	Storage temperature	T <sub>stg</sub>	-55 to +150	°C	





### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

• Tr1

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = 10 \ \mu {\rm A}, I_{\rm E} = 0$	50			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = 2  {\rm mA},  I_{\rm B} = 0$	50			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = 50 \text{ V}, I_E = 0$			1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = 50 \text{ V}, I_{B} = 0$			1	μΑ
Emitter-base cutoff current (Collector open)	I <sub>EBO</sub>	$V_{EB} = 6 V, I_C = 0$			2	mA
Forward current transfer ratio	h <sub>FE</sub>	$V_{CE} = 10 \text{ V}, I_C = 100 \text{ mA}$	50			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = 100 \text{ mA}, I_{\rm B} = 5 \text{ mA}$			0.25	V
Input voltage (ON)	V <sub>I(on)</sub>	$V_{\rm CE} = 0.2$ V, $I_{\rm C} = 50$ mA	3.6			V
Input voltage (OFF)	V <sub>I(off)</sub>	$V_{CE} = 5 \text{ V}, I_C = 100 \mu\text{A}$			0.7	V
Input resistance	R <sub>1</sub>		-30%	4.7	+30%	kΩ
Resistance ratio	R <sub>1</sub> / R <sub>2</sub>		0.8	1.0	1.2	

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

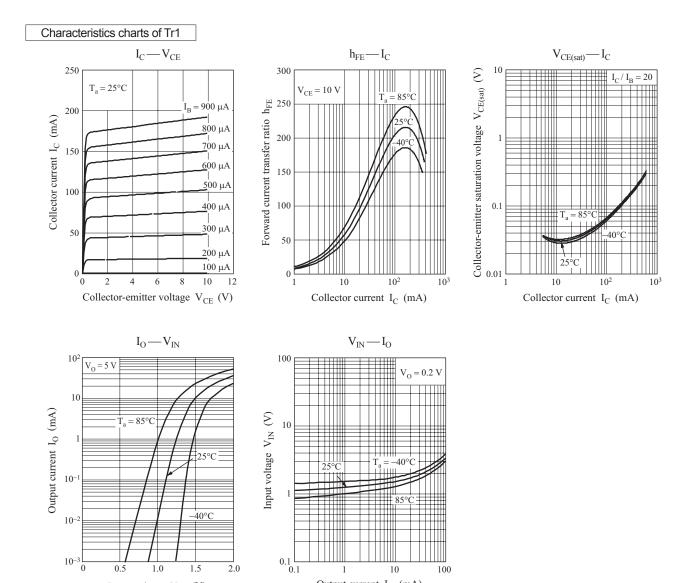
• Tr2

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = -10 \ \mu {\rm A}, I_{\rm E} = 0$	-50			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = -2  {\rm mA},  I_{\rm B} = 0$	-50			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = -50 \text{ V}, I_E = 0$			-1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = -50 \text{ V}, I_B = 0$			-1	μΑ
Emitter-base cutoff current (Collector open)	I <sub>EBO</sub>	$V_{\rm EB} = -6  \text{V},  \text{I}_{\rm C} = 0$			-2	mA
Forward current transfer ratio	$h_{\rm FE}$	$V_{CE} = -10 \text{ V}, I_C = -100 \text{ mA}$	50			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = -100 \text{ mA}, I_{\rm B} = -5 \text{ mA}$			-0.25	V
Input voltage (ON)	V <sub>I(on)</sub>	$V_{\rm CE} = -0.2$ V, $I_{\rm C} = -50$ mA	-3.6			V
Input voltage (OFF)	V <sub>I(off)</sub>	$V_{CE} = -5 \text{ V}, I_C = -100 \mu\text{A}$			-0.7	V
Input resistance	R <sub>1</sub>		-30%	4.7	+30%	kΩ
Resistance ratio	R <sub>1</sub> / R <sub>2</sub>		0.8	1.0	1.2	

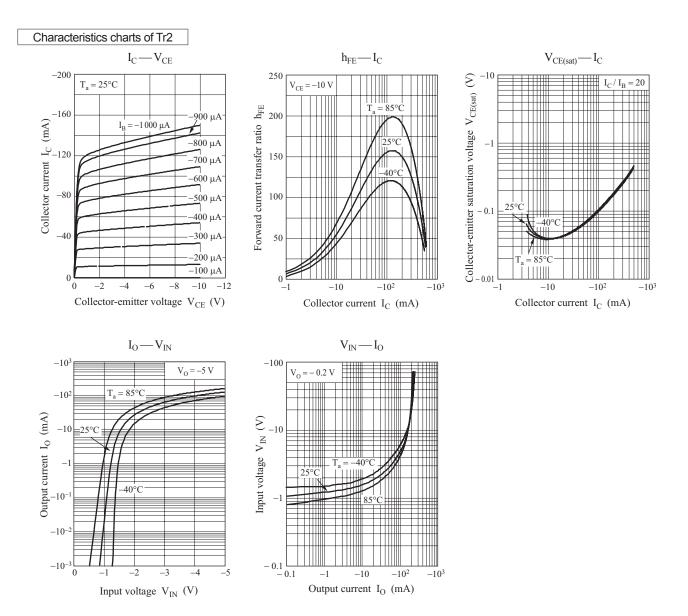
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

Common characteristics chart  $P_T - T_a$ 350 300 Total power dissipation  $P_{\mathrm{T}}$  (mW) 250 200 150 100 50 0 L 0 200 40 80 120 160 Ambient temperature T<sub>a</sub> (°C)

Input voltage V<sub>IN</sub> (V)

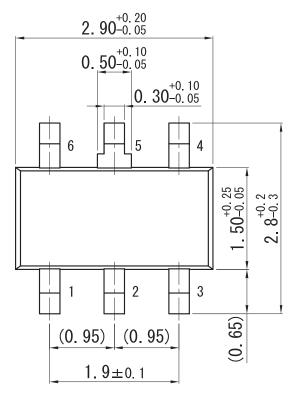


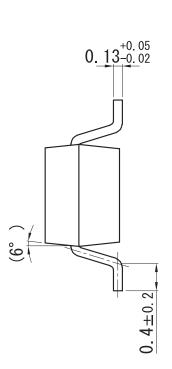
Output current  $I_O$  (mA)

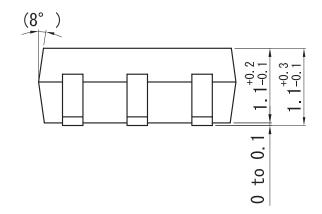


Unit: mm

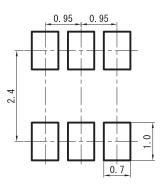
# Mini6-G4-B







Land Pattern (Reference) (Unit: mm)



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